

INCHANGE Semiconductor

ISC Product Specification

isc Silicon PNP Power Transistor

2SA1668

DESCRIPTION

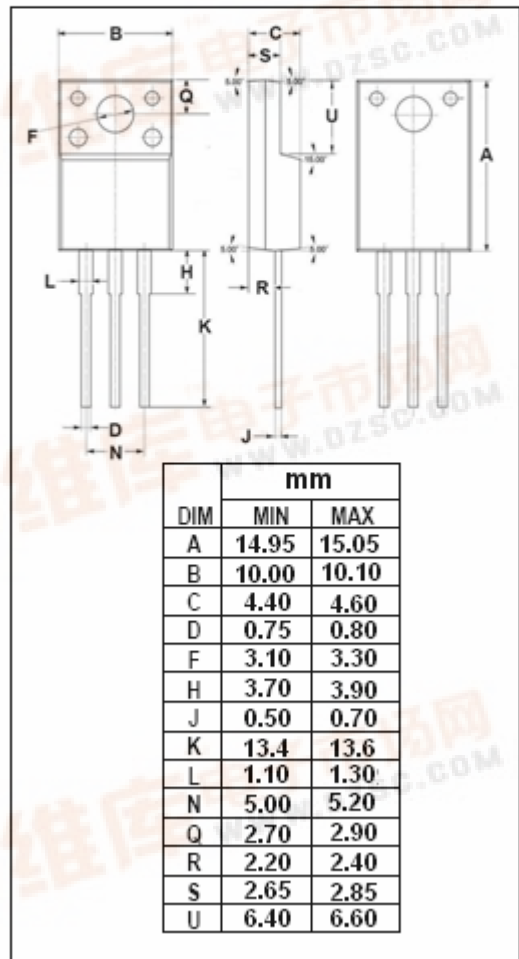
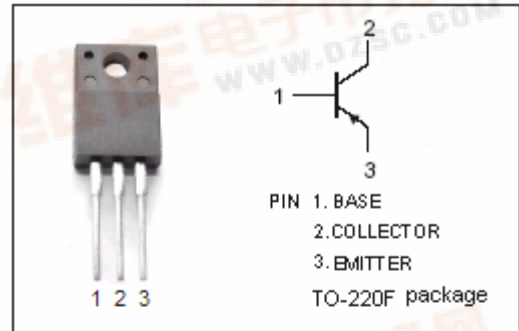
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -200V(\text{Min})$
- DC Current Gain-
: $h_{FE} = 60(\text{Min})@ (V_{CE} = -10V, I_C = -0.7A)$
- Complement to Type 2SC4382

APPLICATIONS

- Designed for TV vertical output ,audio output driver and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-2	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SA1668****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -25mA ; I _B = 0	-200			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.7A; I _B = -0.07A			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -200V ; I _E =0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -6V; I _C =0			-10	μ A
h _{FE}	DC Current Gain	I _C = -0.7A ; V _{CE} = -10V	60			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		60		pF
f _T	Current-Gain—Bandwidth Product	I _E = 0.2A ; V _{CE} = -12V		20		MHz

Switching Times

t _{on}	Turn-On Time	I _C = -1A; I _{B1} = -I _{B2} = -0.1A; V _{CC} = -20V; R _L = 20 Ω		0.4		μ s
t _{stg}	Storage Time			1.5		μ s
t _f	Fall Time			0.5		μ s